



1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 plastic package intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- Air conditioner indoor fan
- General purpose low power motor control
- General purpose switching and phase control

4. Quick reference data

Parameter	Conditions	N	lin	Тур	Мах	Unit
repetitive peak off- state voltage		-		-	800	V
non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-		-	12.5	A
junction temperature		-		-	125	°C
RMS on-state current	full sine wave; $T_{lead} \le 51.2$ °C; Fig. 1; Fig. 2; Fig. 3	-		-	1	A
teristics	· · · · · · · · · · · · · · · · · · ·			•		
gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-		0.4	3	mA
	V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-		1.3	3	mA
	 state voltage non-repetitive peak on- state current junction temperature RMS on-state current 	$\begin{array}{ c c c c c } \mbox{state voltage} & \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	state voltageImagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \ ^{\circ}C$; $t_p = 20 \ ms; Fig. 4; Fig. 5-junction temperature-RMS on-state currentfull sine wave; T_{lead} \le 51.2 \ ^{\circ}C; Fig. 1;Fig. 2; Fig. 3-cteristicsgate trigger currentV_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G+;T_j = 25 \ ^{\circ}C; Fig. 7-V_D = 12 \ V; I_T = 0.1 \ A; T2+ \ G-;-$	$ \begin{array}{ c c c c c } \mbox{state voltage} & & & & & & & & & & & & & & & & & & &$	state voltageImageImageImagenon-repetitive peak on- state currentfull sine wave; $T_{j(init)} = 25 \ ^{\circ}C$; $t_p = 20 \ ^{ms}$; Fig. 4; Fig. 5junction temperatureRMS on-state currentfull sine wave; $T_{lead} \le 51.2 \ ^{\circ}C$; Fig. 1; Fig. 2; Fig. 3certristicsgate trigger current $V_D = 12 \ V$; $I_T = 0.1 \ ^{ch}$; T2+ G+; $T_j = 25 \ ^{\circ}C$; Fig. 7-0.4 $V_D = 12 \ V$; $I_T = 0.1 \ ^{ch}$; T2+ G-;-1.3	$ \begin{array}{ c c c c c } \mbox{state voltage} & \mbox{istate voltage} & \mbox{istate voltage} & \mbox{istate voltage} & \mbox{istate current} & \mbox{full sine wave; $T_{j(init)} = 25 \ ^{\circ}C$;} \\ \mbox{istate current} & \mbox{istate wave; $T_{lead} \le 51.2 \ ^{\circ}C$; $Fig. 1$;} & \mbox{istate current} & \mbox{istate current}$





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{7}$	-	1.4	3	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	3.8	7	mA
Dynamic char	acteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; R _{GT1} = 1 kΩ; (V _{DM} = 67% of V _{DRM}); exponential waveform; Fig. 12	10	20	-	V/µs

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		T2
2	G	gate		sym051
3	T1	main terminal 1	TO-92 (SOT54)	
			10-92 (30194)	

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BT131-800	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				

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7. Limiting values

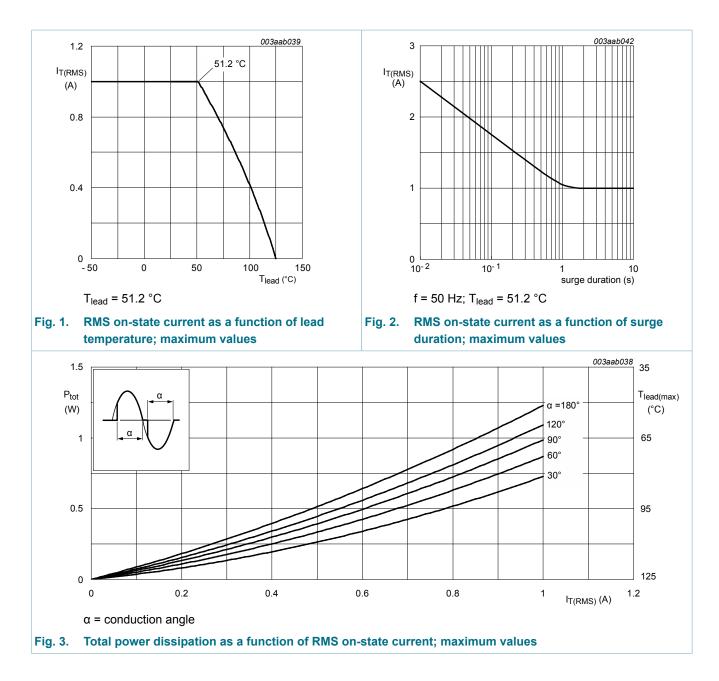
Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 51.2$ °C; Fig. 1; Fig. 2; Fig. 3	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	12.5	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ t _p = 16.7 ms	-	13.7	A
l ² t	I2t for fusing	t _p = 10 ms; sine-wave pulse	-	0.78	A ² s
dI _T /dt rate of rise of on-state current	rate of rise of on-state current	I_T = 1.5 A; I_G = 20 mA; dI_G/dt = 0.2 A/ µs; T2+ G+	-	50	A/µs
	I_T = 1.5 A; I_G = 20 mA; dI_G/dt = 0.2 A/ µs; T2+ G-	-	50	A/µs	
		I_T = 1.5 A; I_G = 20 mA; dI_G/dt = 0.2 A/ µs; T2- G-	-	50	A/µs
		I_T = 1.5 A; I_G = 20 mA; dI_G/dt = 0.2 A/ µs; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

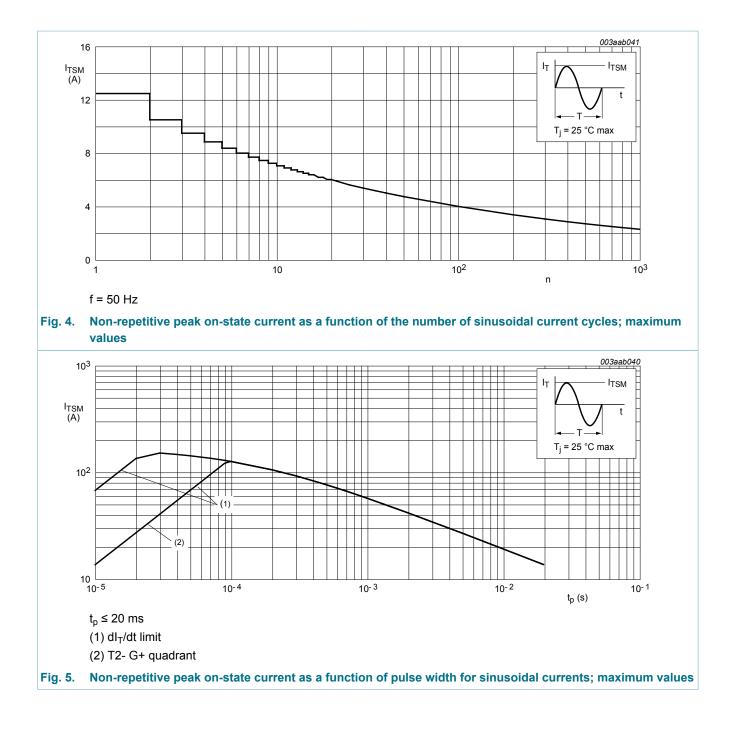
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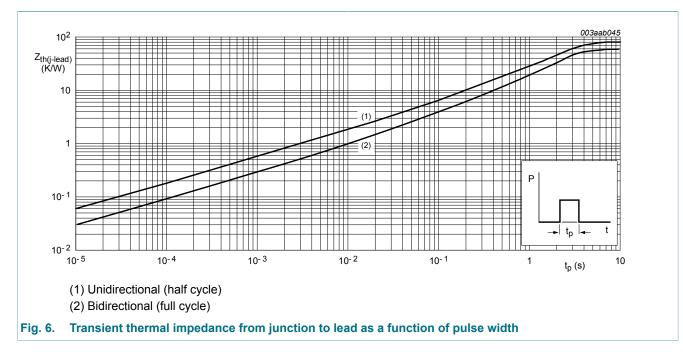
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8. Thermal characteristics

Table 5. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	full cycle; <u>Fig. 6</u>	-	-	60	K/W
		half cycle; <u>Fig. 6</u>	-	-	80	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



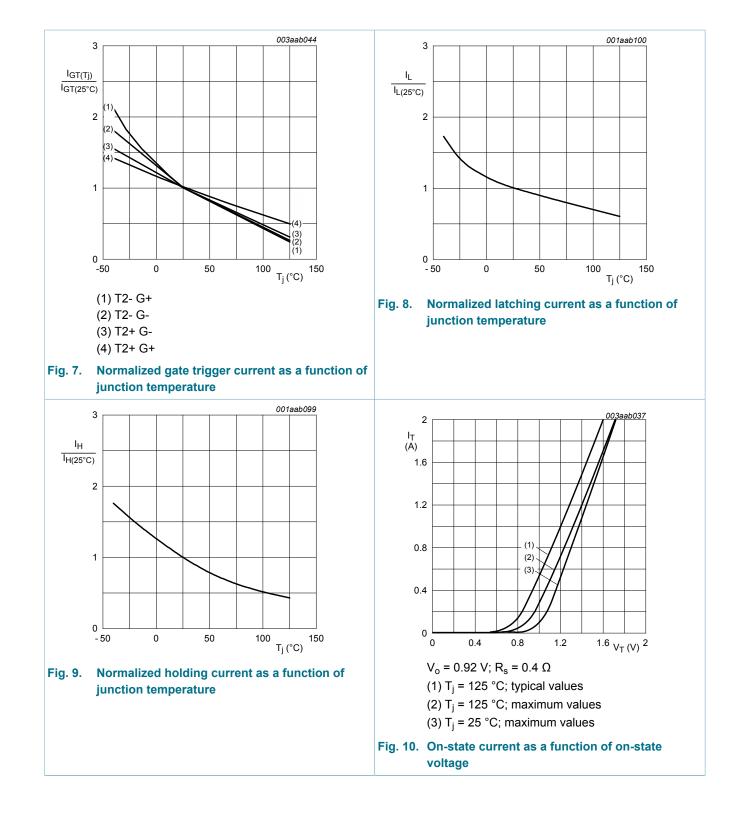
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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
I _{GT}	gate trigger current	V_D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	0.4	3	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 7</u>	-	1.3	3	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	1.4	3	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 7</u>	-	3.8	7	mA
I _L latching	latching current	V_D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	1.2	5	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; <u>Fig. 8</u>	-	4	8	mA
		V _D = 12 V; I _G = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 8</u>	-	1	5	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; <u>Fig. 8</u>	-	2.5	8	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	1.3	5	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 0.1 A; T _j = 25 °C; Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.2	0.3	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·				
dV _D /dt	rate of rise of off-state voltage	$\label{eq:VDM} \begin{split} V_{DM} &= 536 \text{ V}; \text{T}_{\text{j}} = 125 ^{\circ}\text{C}; \text{R}_{\text{GT1}} = 1 \text{k}\Omega; \\ (V_{DM} &= 67\% \text{ of } V_{DRM}); \text{ exponential} \\ \text{waveform; } \text{Fig. 12} \end{split}$	10	20	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ dI}_{com}/$ dt = 0.5 A/ms; I _T = 1 A	2	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1.5 A; V _D = 800 V; I _G = 0.1 A; dI _G / dt = 5 A/µs	-	2	-	μs

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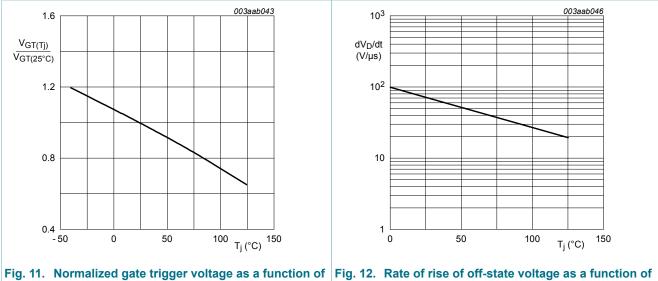
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junction temperature

. Rate of rise of off-state voltage as a function of junction temperature; minimum values

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10. Package outline

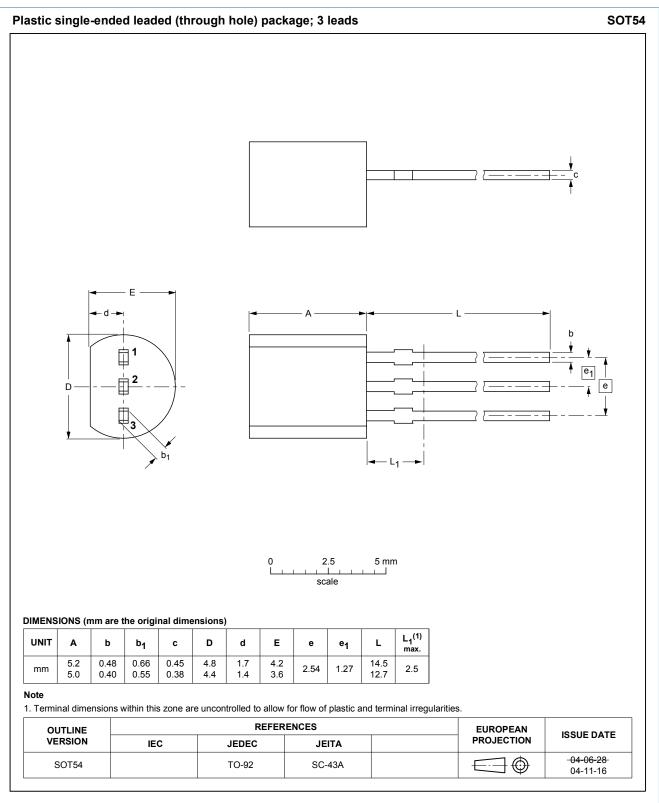


Fig. 13. Package outline TO-92 (SOT54) BT131-800 All

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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